

**MIXED-DOMAIN MULTI-SIMULATOR  
STATISTICAL DEVICE MODELING  
AND YIELD-DRIVEN DESIGN**

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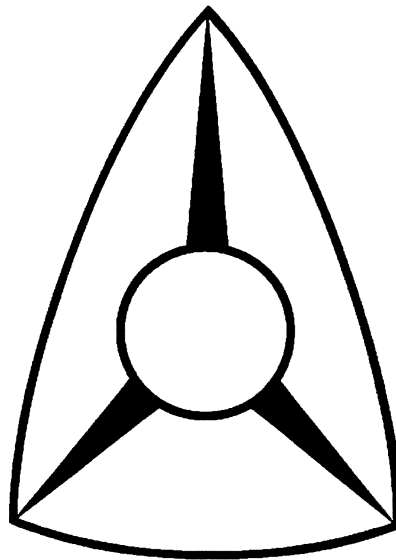
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# **MIXED-DOMAIN MULTI-SIMULATOR STATISTICAL DEVICE MODELING AND YIELD-DRIVEN DESIGN**

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## **Introduction**

statistical modeling and design are indispensable for today's microwave CAD, especially for MMIC design

taking into account manufacturing tolerances and model uncertainties

microwave designers are forced to use different CAD systems to address different aspects of their designs; tedious and time consuming because of incompatible user interfaces and data formats

public domain SPICE does not provide means for optimization; rigid structure of commercial versions of SPICE permits only limited optimization

intelligent computational interfaces are needed

we present a flexible approach to mixed-domain, multi-simulator statistical modeling and design

we integrate time-domain, frequency-domain and EM simulations into a versatile optimization environment



## Outline

Datapipe - an open architecture interface to connect various CAD systems in a uniform and user-friendly manner

mixed-domain, multi-simulator approach to device modeling and yield-driven optimization

theory

simple example

integrating SPICE device models, Sonnet's *em* electromagnetic simulations and OSA's OSA90/hope circuit level optimization

statistical modeling of GaAs MESFETs  
yield optimization

Space Mapping optimization to align mode-matching and finite element based electromagnetic simulations



## **Datapipe Technique for Optimization Interface**

utilizes interprocess pipe communication

establishes high speed data connections between different processes

communication with each child

Datapipe protocol at the parent side

Datapipe server at the child side

a set of communication standards defines the sequence and meaning of the data fields exchanged between the parent and the child

the parent and the child can be totally independent

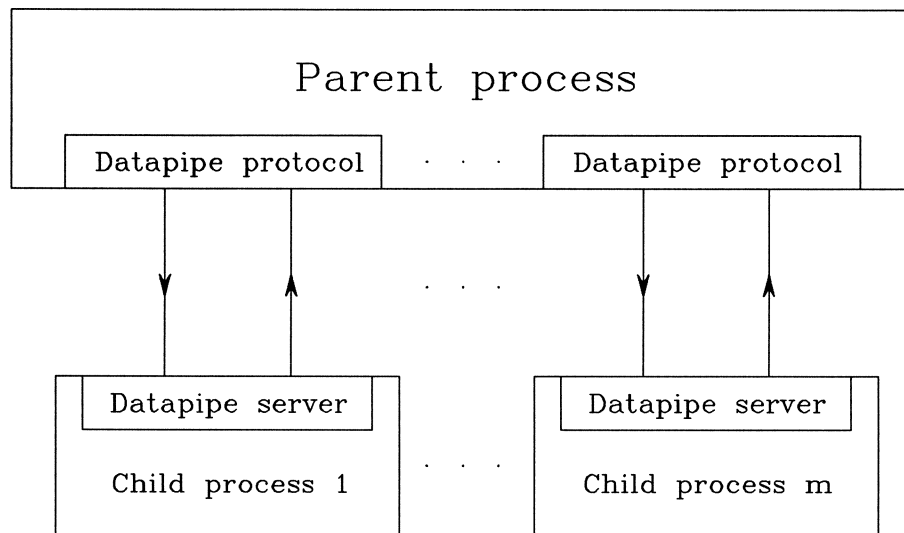
source code does not need to be revealed (suitable for sensitive software)

no limit to the number of children connected with a single parent

the parent and the children can communicate through a network of computers



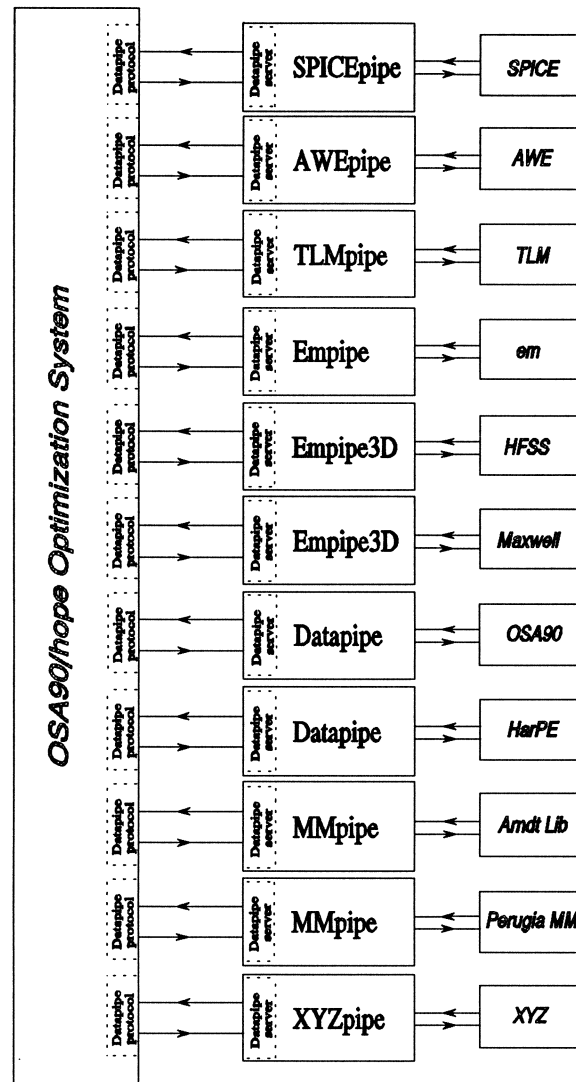
## **Datapipe Schematic**



**Datapipe interface between a parent process and a number of child processes**



## OSA90/hope Connections



Datapipe interfaces between OSA90/hope and several external simulators, including SPICE (public domain), AWE (*Carleton University*), TLM (*University of Victoria*), *em* (*Sonnet Software*), HFSS (*Ansoft, HP-EEsof*) and RWGMM (*Arndt, University of Bremen*)



## **Mixed-Domain Multi-Simulator Yield-Driven Design**

$n_o$  outcomes are used in yield optimization

for all outcomes  $\phi^i$  the parent integrates the results returned from each child and performs the circuit-level simulation

$$R_P(\phi^i) = R_P(\phi^i, R_{C_1}(\phi^i), R_{C_2}(\phi^i), \dots, R_{C_m}(\phi^i))$$

where

$R_P$  circuit-level responses simulated by the parent  
 $R_{C_k}$  subcircuits simulated by the  $k$ th child

in general

$$R_{C_k}(\phi^i) = R_{C_k}(R_{C_k}^t(\phi^i), R_{C_k}^f(\phi^i), R_{C_k}^e(\phi^i))$$

where

$R_{C_k}^t$  time-domain responses  
 $R_{C_k}^f$  frequency-domain responses  
 $R_{C_k}^e$  EM responses

each child is usually devoted to only one particular type of simulation





## **Formulation for Yield-Driven Design**

error functions

$$e_j(\boldsymbol{\phi}^i) = R_{P_j}(\boldsymbol{\phi}^i) - S_j \quad \text{upper specifications}$$

$$e_j(\boldsymbol{\phi}^i) = S_j - R_{P_j}(\boldsymbol{\phi}^i) \quad \text{lower specifications}$$

for all outcomes  $\boldsymbol{\phi}^i$  and all specifications  $S_j, j = 1, 2, \dots, n_s$

outcome  $\boldsymbol{\phi}^i$  is acceptable if all  $e_j(\boldsymbol{\phi}^i), j = 1, 2, \dots, n_s$ , are nonpositive (all design specifications are satisfied)

design yield

the ratio of acceptable outcomes to the total number of outcomes considered

yield-driven design formulation

$$\underset{\boldsymbol{\phi}^0}{\text{minimize}} \quad U(\boldsymbol{\phi}^0) = \sum_{i=1}^{n_o} H[\alpha_i \nu(\boldsymbol{\phi}^i)]$$

where

$\alpha_i$             positive multipliers

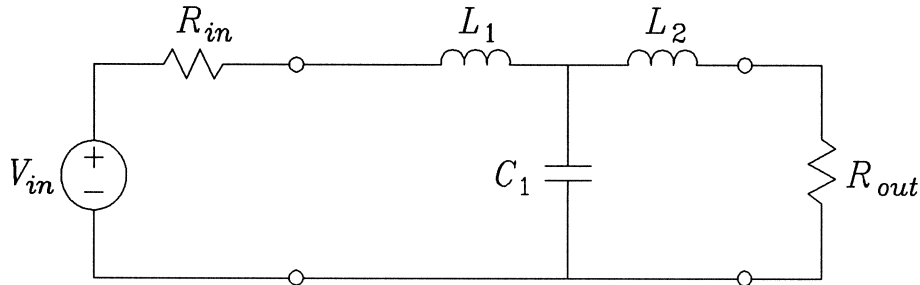
$\nu(\boldsymbol{\phi}^i)$         the generalized  $\ell_p$  function

$H$                 one-sided  $\ell_1$  or one-sided Huber



## **Mixed-Domain Multi-Simulator Yield-Driven Design: Example**

a simple low-pass filter



specifications defined in the frequency domain

$$\begin{array}{ll} \text{insertion loss} \leq 1.5 \text{ dB} & \text{for } 0 < \omega < 1 \\ \text{insertion loss} \geq 25 \text{ dB} & \text{for } \omega > 2.5 \end{array}$$

and in the time domain

$$0.45 \text{ V} \leq V_{out} \leq 0.55 \text{ V} \quad \text{for } 3.5 \text{ s} < t < 20 \text{ s}$$

design variables:  $L_1$ ,  $L_2$  and  $C_1$  with a uniform distribution within a 10% tolerance

time-domain simulation performed by SPICE

frequency-domain simulation performed by OSA90/hope

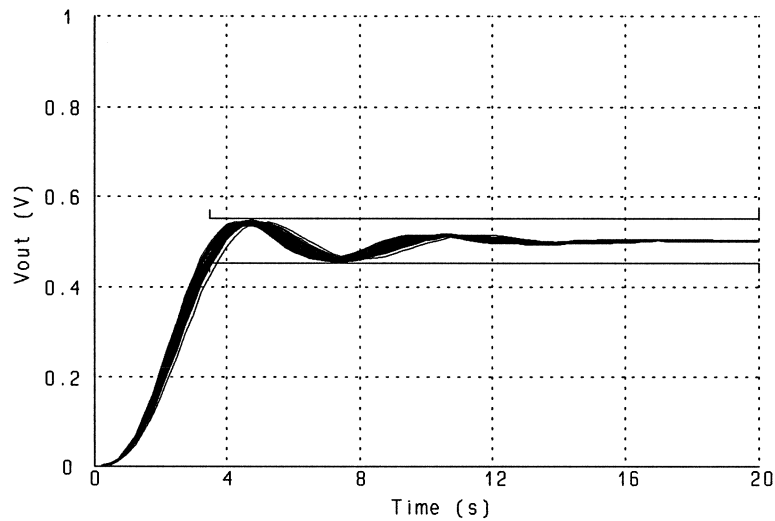
mixed-domain optimization performed by OSA90/hope

nominal design followed by yield optimization

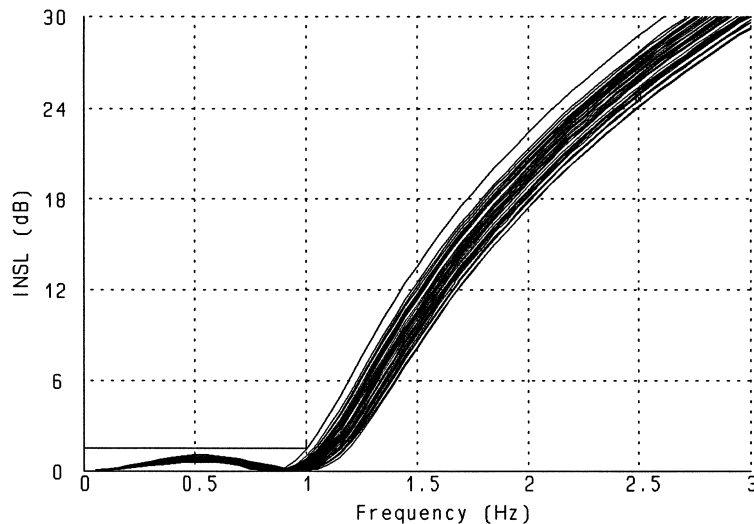


## **Statistical Responses of the Low-Pass Filter**

time-domain Monte Carlo sweep



frequency-domain Monte Carlo sweep



yield is increased from 29% at the nominal design to 67% after optimization



## **Capturing SPICE Device Models**

SPICE is invoked to simulate individual devices only

to obtain  $S$  parameters we invoke SPICE evaluation of node voltages

two SPICE simulations determine the parameters of a 2-port network

SPICE output returned to OSA90/hope may need to be postprocessed

the node voltages are converted to the  $S$  parameters using mathematical expressions in the OSA90/hope input file



**Error Functions for Statistical Device Modeling with SPICE**  
(Bandler et al., *Int. J. MIMICAE*, 1997)

measurement data

$$S^i = [S_1^i \ S_2^i \ \dots \ S_{n_i}^i]^T, \quad i = 1, 2, \dots, n_d$$

$n_d$  sets of data measured from  $n_d$  devices

$n_i$  measured responses in the  $i$ th data set

the corresponding SPICE responses

$$R_{SP}(\phi^i) = [R_{SP_1}(\phi^i) \ R_{SP_2}(\phi^i) \ \dots \ R_{SP_{n_i}}(\phi^i)]^T$$

where  $\phi^i$  is the  $i$ th set of model parameters to be extracted

for each data set, the error vector is defined as

$$e_{OS}(\phi^i) = [e_{OS_1}(\phi^i) \ e_{OS_2}(\phi^i) \ \dots \ e_{OS_{n_i}}(\phi^i)]^T$$

individual errors represent the equality constraints of the matching problem

$$e_{OS_j}(\phi^i) = R_{SP_j}(\phi^i) - S_j^i$$



## **Parameter Extraction for Individual Outcomes**

$$\underset{\phi^i}{\text{minimize}} \quad U_{OS}(\phi^i)$$

$U_{OS}$  is an objective function such as the  $\ell_1$ ,  $\ell_2$  or the Huber norm

## **Statistical Postprocessing**

to derive the statistical model

for each device outcome the parameter extraction is driven by OSA90/hope's optimizer with the device model captured from SPICE

repeated for each data set, it leads to a sample of individually extracted device models

the model statistics including the mean values, standard deviations and the correlation matrix are produced by postprocessing this sample of models



## **Statistical Modeling of a GaAs MESFET**

measurement data for a sample of a GaAs MESFET

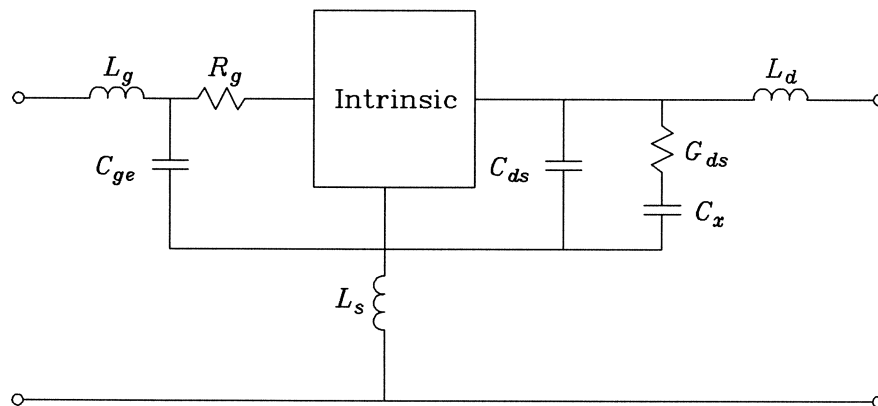
35 data sets (devices)

small-signal  $S$  parameters at frequencies from 1 to 21 GHz  
with a 2 GHz step

under two bias conditions

the wafer measurements aligned to consistent bias conditions

the equivalent circuit to model the GaAs MESFET



18 model parameters



## **Results of Statistical Modeling of a GaAs MESFET**

### **MEAN VALUES AND STANDARD DEVIATIONS FOR THE STATISTICAL SPICE MESFET MODEL**

Parameter	Mean	Standard Deviation (%)
$C_{gs}$ (pF)	0.4651	2.87
$C_{gd}$ (pF)	0.0293	2.52
$\lambda$ (1/V)	$4.046 \times 10^{-3}$	9.75
$V_{to}$ (V)	-2.4863	5.32
$\beta$ (A/V <sup>2</sup> )	0.0135	5.64
$B$ (1/V)	$2.3032 \times 10^{-3}$	9.44
$\alpha$ (1/V)	1.9413	7.61
$R_d$ ( $\Omega$ )	0.0111	8.35
$R_s$ ( $\Omega$ )	6.5941	5.15
$PB$ (V)	0.6279	7.80
$R_g$ ( $\Omega$ )	3.7129	6.62
$G_{ds}$ (1/ $\Omega$ )	$3.5593 \times 10^{-3}$	2.28
$C_{ds}$ (pF)	0.0485	2.50
$L_g$ (nH)	0.0306	7.97
$L_d$ (nH)	0.0783	9.11
$L_s$ (nH)	0.0344	3.40
$C_{ge}$ (pF)	0.0379	9.96
$C_x$ (pF)	20.0	-

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$C_{gs}$  through  $PB$  are the intrinsic SPICE MESFET parameters.  
 $R_g$  through  $C_x$  are extrinsic parameters.  $C_x$  is non-statistical.

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## **Verification of the Statistical Model**

the complete statistics include the mean values, standard deviations, discrete density functions (DDF) and the correlation matrix

comparing the statistics of the model responses estimated by Monte Carlo simulation with those of the data

*S* parameters at 11 GHz

bias point:  $V_G = -0.5$  V,  $V_D = 5$  V

MEAN VALUES AND STANDARD DEVIATIONS OF  
DATA AND SPICE MODEL RESPONSES

	Data		SPICE MODEL	
	Mean	Dev. (%)	Mean	Dev. (%)
$Re\{S_{11}\}$	-0.197	9.18	-0.192	12.5
$Im\{S_{11}\}$	-0.756	1.1	-0.747	1.07
$Re\{S_{12}\}$	0.0733	2.7	0.0770	3.1
$Im\{S_{12}\}$	0.0519	2.36	0.0527	4.89
$Re\{S_{21}\}$	-0.212	8.35	-0.432	15.2
$Im\{S_{21}\}$	1.78	1.22	1.736	8.71
$Re\{S_{22}\}$	0.440	1.43	0.434	3.33
$Im\{S_{22}\}$	-0.364	0.89	-0.364	0.96
$I_d$ (A)	0.0401	8.16	0.0407	14.7



## **Verification of the Statistical Model (cont'd)**

*S* parameters at 11 GHz

bias point:  $V_G = -0.7$  V,  $V_D = 5$  V

MEAN VALUES AND STANDARD DEVIATIONS OF  
DATA AND SPICE MODEL RESPONSES

	Data		SPICE MODEL	
	Mean	Dev. (%)	Mean	Dev. (%)
$Re\{S_{11}\}$	-0.153	12.1	-0.170	13.7
$Im\{S_{11}\}$	-0.764	1.0	-0.760	1.01
$Re\{S_{12}\}$	0.0770	2.71	0.0784	2.93
$Im\{S_{12}\}$	0.0559	2.46	-0.054	4.68
$Re\{S_{21}\}$	-0.230	6.99	-0.433	15.3
$Im\{S_{21}\}$	1.687	1.67	1.650	9.22
$Re\{S_{22}\}$	0.439	1.44	0.442	3.27
$Im\{S_{22}\}$	-0.367	0.89	-0.366	0.97
$I_d$ (A)	0.0332	9.51	0.0338	16.1

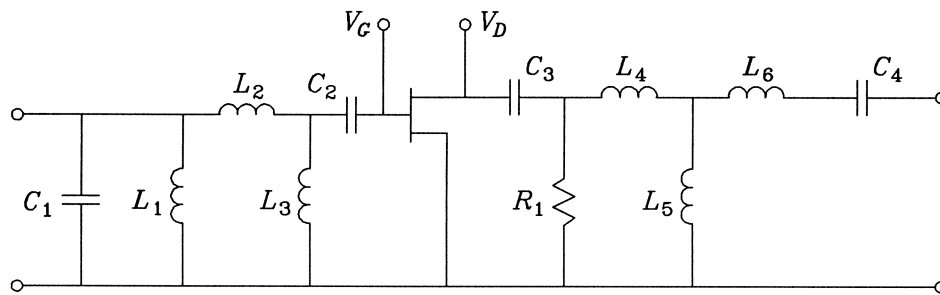
very good agreement between data and the model responses  
for the mean values

some discrepancies in standard deviations are likely due the  
inadequate statistical modeling capabilities of equivalent  
circuit models



## **Yield-Driven Design of an Amplifier**

a small-signal amplifier



design specifications (for frequencies from 8 to 12 GHz)

$$\begin{aligned} 7.25 \text{ dB} &< |S_{21}| < 8.75 \text{ dB} \\ |S_{11}| &< 0.5 \\ |S_{22}| &< 0.5 \end{aligned}$$

design variables

the matching circuit elements  $L_1, L_2, L_3, L_4, L_5, L_6, C_1, C_2, C_3, C_4$  and  $R_1$

28 statistical parameters

uniform distribution within a 5% tolerance

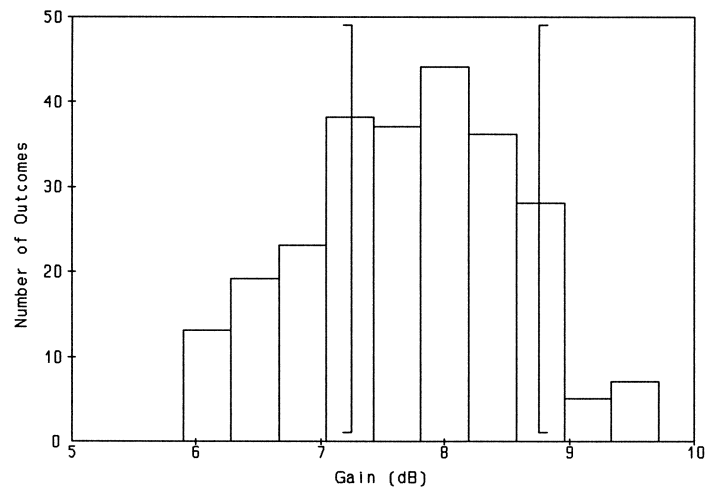
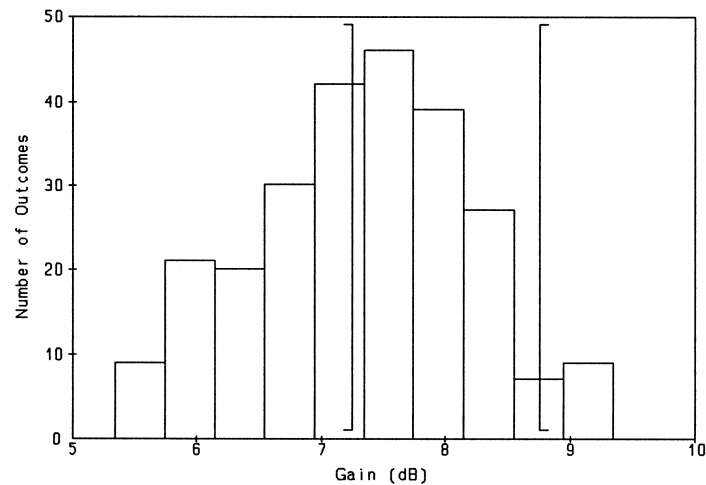
the MESFET is simulated in SPICE

SPICE results are returned to OSA90/hope through Spicpipe for circuit-level simulation and optimization



## **Histograms Before and After Yield Optimization**

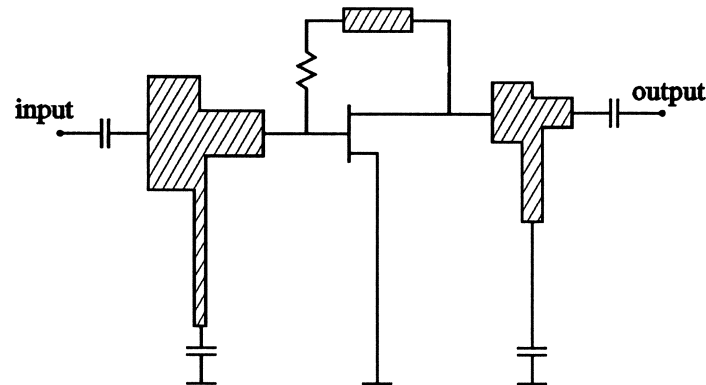
**$|S_{21}|$  at 12 GHz**



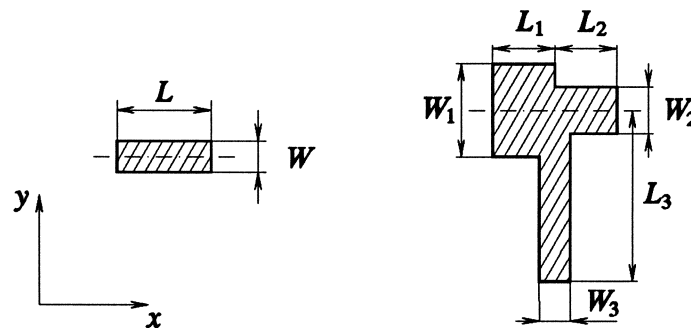
yield is increased from 16% at the nominal design to 52% after optimization



## A Broadband Small-Signal Amplifier



parameters of the feedback microstrip line and the microstrip  $T$ -structures



design specifications

$$7 \text{ dB} \leq |S_{21}| \leq 8 \text{ dB} \quad \text{for} \quad 6 \text{ GHz} \leq f \leq 18 \text{ GHz}$$

design variables

gate  $T$ -structure:  $W_{g1}, L_{g1}, W_{g2}, L_{g2}$

drain  $T$ -structure:  $W_{d1}, L_{d1}, W_{d2}, L_{d2}$



**Combined *em*/SPICE Yield-Driven Design**  
(Bandler *et al.*, *Int. J. MIMICAE*, 1997)

the MESFET simulated by SPICE

microstrip components accurately simulated by Sonnet's *em*

the line and the *T*-structure primitives of the Empipe  
library are invoked

circuit-level simulation and optimization carried out by  
OSA90/hope

uniform distribution within a 0.5 mil tolerance for all  
geometrical parameters

yield at the nominal minimax solution is 43%

yield is increased to 74% after yield optimization

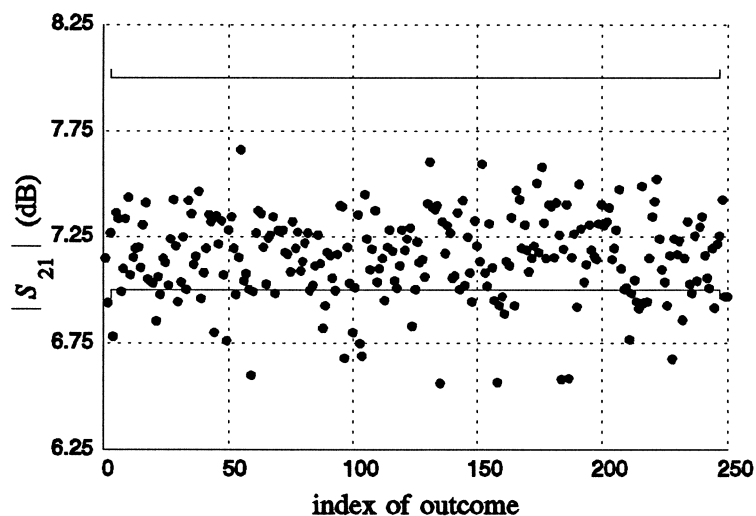
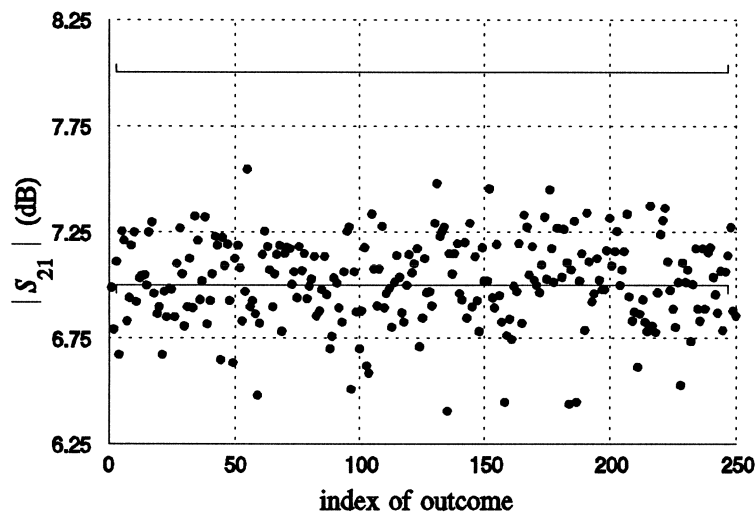
50 outcomes used for yield optimization



## Run Charts Before and After Yield Optimization

$|S_{21}|$  at 18 GHz

250 outcomes



clearly, many more outcomes meet the specification after yield optimization



## **Space Mapping Optimization**

to avoid direct optimization of computationally intensive models

the multi-simulator approach is particularly relevant and suitable for Space Mapping

automatic alignment of two distinct models of different accuracy and computational efficiency

such models would normally be facilitated by two disjoint simulators

two different EM simulators are used here

EM space or "fine" model - 3D FEM-based field simulator Maxwell Eminence (*Ansoft Corp.*)

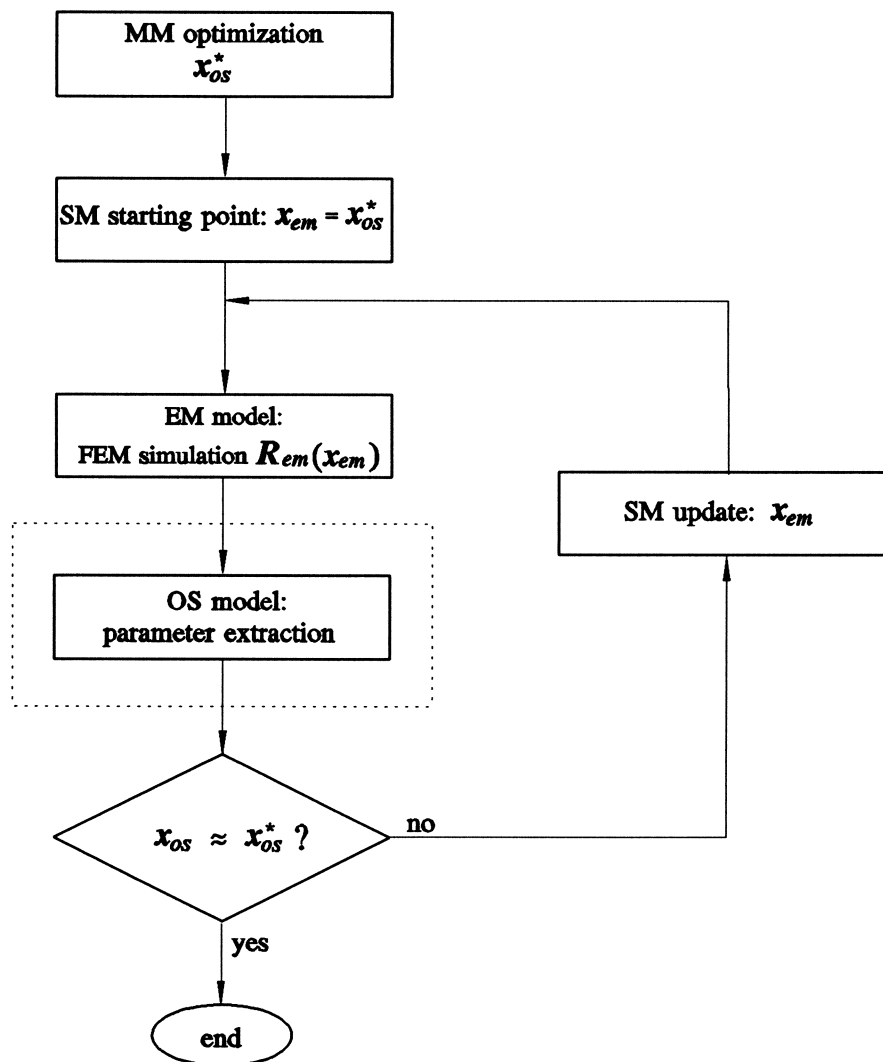
optimization space (OS) or "coarse" model - the RWGMM library of waveguide mode-matching (MM) models connected by network theory (*Fritz Arndt*)





## Space Mapping Using MM/Network Theory and FEM (Bandler et al., 1997 Int. Microwave Symp.)

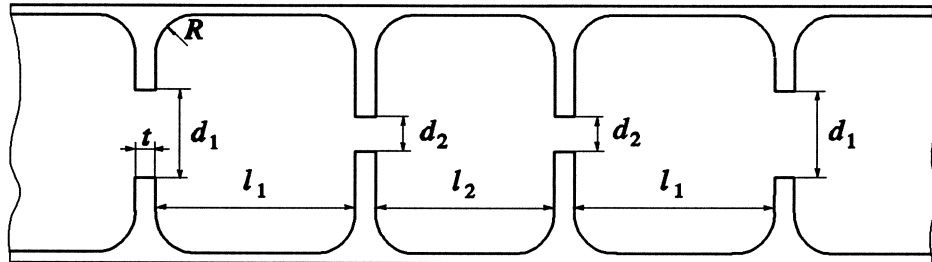
flow diagram of Space Mapping concurrently exploiting the hybrid MM/network theory and FEM simulation techniques



two-level Datapipe architecture



## **Optimization of an H-Plane Resonator Filter**



the waveguide cross-section:  $15.8 \times 7.9$  mm

iris and corner radius:  $t = 0.4$  mm,  $R = 1$  mm

design variables

$$d_1, d_2, l_1 \text{ and } l_2$$

design specifications

$$\begin{array}{lll} |S_{21}| < -35 \text{ dB} & \text{for} & 13.5 \leq f \leq 13.6 \text{ GHz} \\ |S_{11}| < -20 \text{ dB} & \text{for} & 14.0 \leq f \leq 14.2 \text{ GHz} \\ |S_{21}| < -35 \text{ dB} & \text{for} & 14.6 \leq f \leq 14.8 \text{ GHz} \end{array}$$

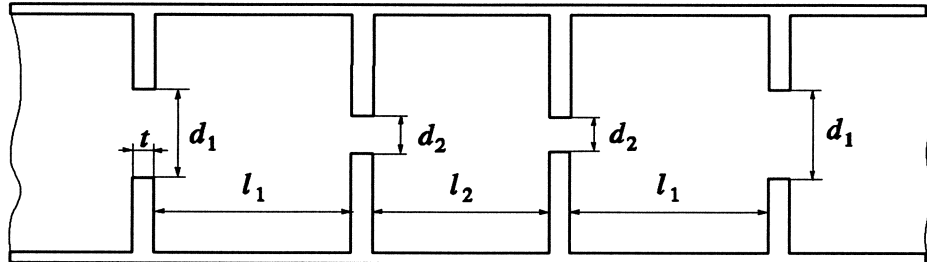
FEM analysis - fine (or EM) model for Space Mapping

capable of analyzing arbitrary shapes

computationally very intensive



## Coarse Model for Space Mapping Optimization



OS model (coarse model) for Space Mapping

sharp corners

hybrid MM/network theory simulation

computationally efficient

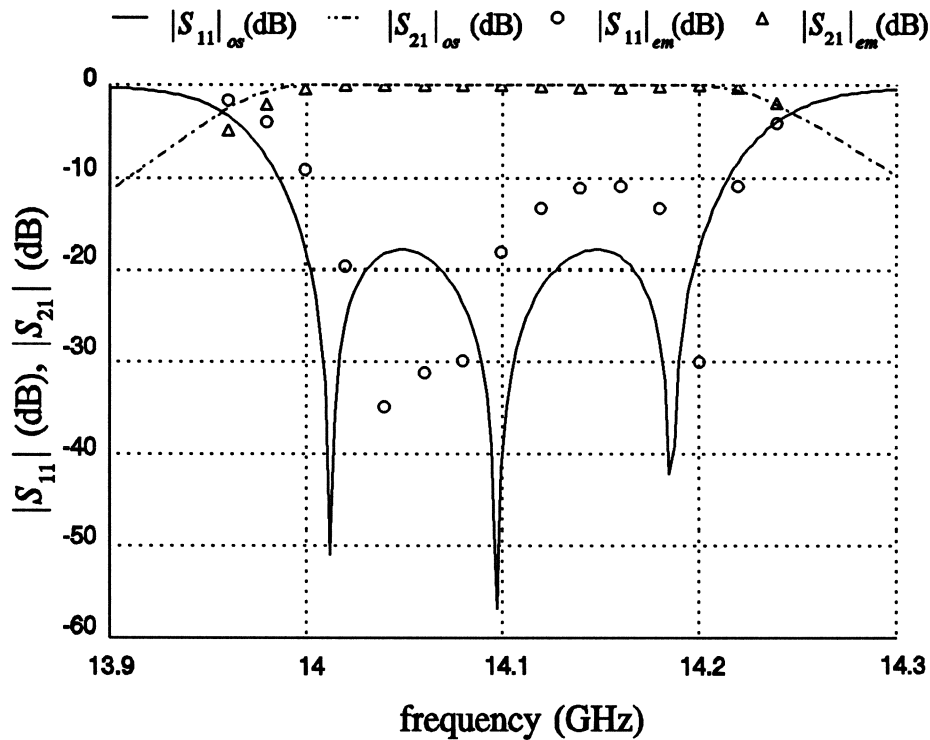
accurately treats a variety of predefined geometries

ideally suited for modeling complex waveguide  
structures decomposable into available library building  
blocks

minimax optimization of the OS model gives the starting  
point for Space Mapping



## Responses at the Starting Point



focus on the passband: 13.96 to 14.24 GHz

RWGMM (curves) and Maxwell Eminence (points)

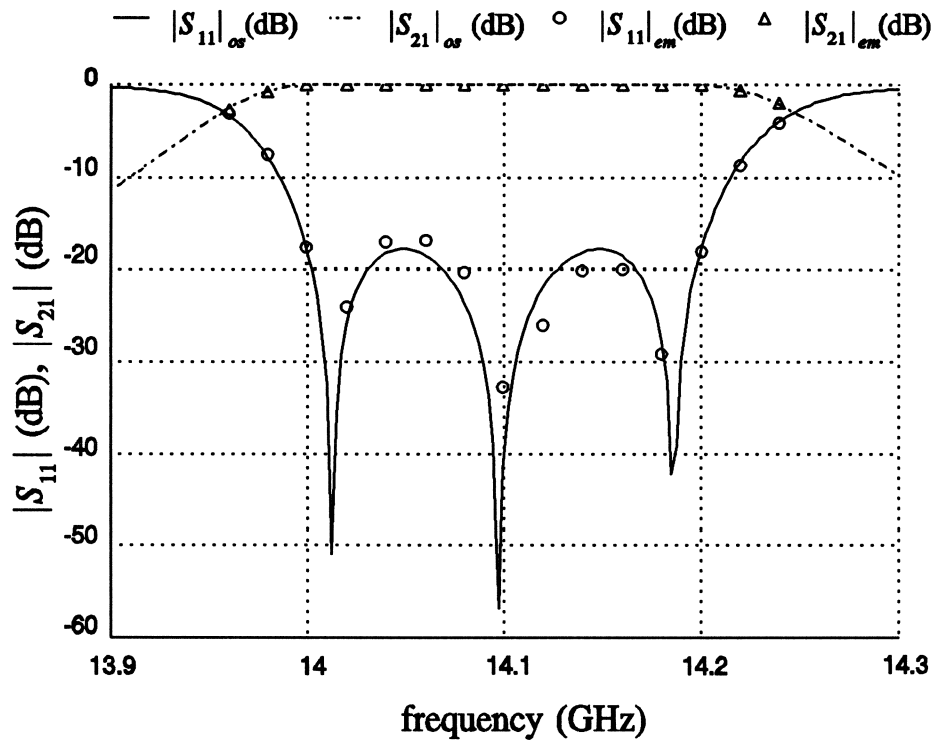
discrepancy is evident

$$d_1 = 6.04541, d_2 = 3.21811, l_1 = 13.0688 \text{ and } l_2 = 13.8841$$

the minimax solution in the OS space,  $\mathbf{x}_{os}^*$ , yields the target response for Space Mapping



## SM Optimized FEM Responses



only 4 Maxwell Eminence simulations

RWGMM (curves) and Maxwell Eminence (points)

very good match

$d_1 = 6.17557$ ,  $d_2 = 3.29058$ ,  $l_1 = 13.0282$  and  $l_2 = 13.8841$

direct optimization using Empipe3D confirms that the Space Mapping solution is indeed optimal



## **Conclusions**

based on the Datapipe open architecture, intelligent computational interfaces combine and enhance the features of otherwise disjoint simulators

time-domain, frequency-domain and EM simulations are integrated for efficient statistical modeling and design

mixed-domain specifications illustrated by design of a simple low-pass filter with specifications in both the time and frequency domains

statistical device modeling: SPICE models captured by OSA90/hope's optimizers

design of a broadband amplifier with microstrip components: the MESFET is simulated by SPICE and the microstrip components are analyzed by *em*

further advantages of the multi-simulator approach are exemplified by Space Mapping optimization with two different EM simulators: mode-matching and finite element